

## HEXFRED® Ultrafast Soft Recovery Diode, 60 A


**SOT-227**
**FEATURES**

- Fast recovery time characteristic
- Electrically isolated base plate
- Antiparallel diodes
- Large creepage distance between terminal
- Simplified mechanical designs, rapid assembly
- UL approved file E78996
- Compliant to RoHS directive 2002/95/EC
- Designed and qualified for industrial level


**RoHS  
COMPLIANT**
**PRODUCT SUMMARY**

|                      |                |
|----------------------|----------------|
| $V_R$                | 1200 V         |
| $V_F$ (typical)      | 2.2 V          |
| $t_{rr}$ (typical)   | 145 ns         |
| $I_{F(DC)}$ at $T_C$ | 30 A at 120 °C |

**DESCRIPTION/APPLICATIONS**

This SOT-227 modules with HEXFRED® rectifier are in antiparallel configuration. The antiparallel configuration is used for simple series rectifier and high voltage application. The semiconductor in the SOT-227 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built.

These modules are intended for general applications such as HV power supplies, electronic welders, motor control and inverters.

**ABSOLUTE MAXIMUM RATINGS**

| PARAMETER  | SYMBOL         | TEST CONDITIONS   | MAX.        | UNITS |
|--|----------------|---|-------------|-------|
| Cathode to anode voltage                         | $V_R$          |   | 1200        | V     |
| Continuous forward current                       | $I_F$          | $T_C = 120\text{ °C}$                                   | 30          | A     |
| Single pulse forward current                     | $I_{FSM}$      | $T_J = 25\text{ °C}$                                    | 350         |       |
| Maximum repetitive forward current               | $I_{FRM}$      | Rated $V_R$ , square wave, 20 kHz, $T_C = 60\text{ °C}$ | 130         |       |
| Maximum power dissipation                        | $P_D$          | $T_C = 25\text{ °C}$                                    | 312         | W     |
|  |                | $T_C = 100\text{ °C}$                                   | 125         |       |
| RMS isolation voltage                            | $V_{ISOL}$     | Any terminal to case, $t = 1\text{ minute}$             | 2500        | V     |
| Operating junction and storage temperature range | $T_J, T_{Stg}$ |   | - 55 to 150 | °C    |

**ELECTRICAL SPECIFICATIONS ( $T_J = 25\text{ °C}$  unless otherwise specified)**

| PARAMETER                          | SYMBOL   | TEST CONDITIONS                               | MIN. | TYP. | MAX. | UNITS         |
|------------------------------------|----------|---|------|------|------|---------------|
| Cathode to anode breakdown voltage | $V_{BR}$ | $I_R = 100\text{ }\mu\text{A}$                | 1200 | -    | -    | V             |
| Forward voltage                    | $V_{FM}$ | $I_F = 30\text{ A}$                           | -    | 2.2  | 3.0  |               |
|                                    |          | $I_F = 60\text{ A}$                           | -    | 2.7  | 3.8  |               |
| Reverse leakage current            | $I_{RM}$ | $V_R = V_R\text{ rated}$                      | -    | 2.0  | 75   | $\mu\text{A}$ |
|                                    |          | $T_J = 150\text{ °C}, V_R = V_R\text{ rated}$ | -    | 2.7  | 10   | mA            |

| DYNAMIC RECOVERY CHARACTERISTICS ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified) |           |                                   |  |      |      |      |       |
|---|-----------|-----------------------------------|--|------|------|------|-------|
| PARAMETER   | SYMBOL    | TEST CONDITIONS                   |  | MIN. | TYP. | MAX. | UNITS |
| Reverse recovery time   | $t_{rr}$  | $T_J = 25\text{ }^\circ\text{C}$  | $I_F = 50\text{ A}$<br>$dI_F/dt = -200\text{ A}/\mu\text{s}$<br>$V_R = 200\text{ V}$ | -    | 145  | -    | ns    |
|   |           | $T_J = 125\text{ }^\circ\text{C}$ |  | -    | 218  | -    |       |
| Peak recovery current   | $I_{RRM}$ | $T_J = 25\text{ }^\circ\text{C}$  |  | -    | 13   | -    | A     |
|   |           | $T_J = 125\text{ }^\circ\text{C}$ |  | -    | 19   | -    |       |
| Reverse recovery charge   | $Q_{rr}$  | $T_J = 25\text{ }^\circ\text{C}$  |  | -    | 910  | -    | nC    |
|   |           | $T_J = 125\text{ }^\circ\text{C}$ |  | -    | 1920 | -    |       |

| THERMAL - MECHANICAL SPECIFICATIONS     |            |                           |      |      |      |                           |
|---|------------|---------------------------|------|------|------|---------------------------|
| PARAMETER                               | SYMBOL     | TEST CONDITIONS           | MIN. | TYP. | MAX. | UNITS                     |
| Junction to case, single leg conducting | $R_{thJC}$ |                           | -    | -    | 0.4  | $^\circ\text{C}/\text{W}$ |
| Junction to case, both legs conducting  |            |                           | -    | -    | 0.2  |                           |
| Case to heatsink                        | $R_{thCS}$ | Flat, greased and surface | -    | 0.05 | -    |                           |
| Weight                                  |            |                           | -    | 30   | -    | g                         |
| Mounting torque                         |            |                           | -    | 1.3  | -    | Nm                        |

**HEXFRED®**  
 Ultrafast Soft Recovery Diode, 60 A

Vishay Semiconductors

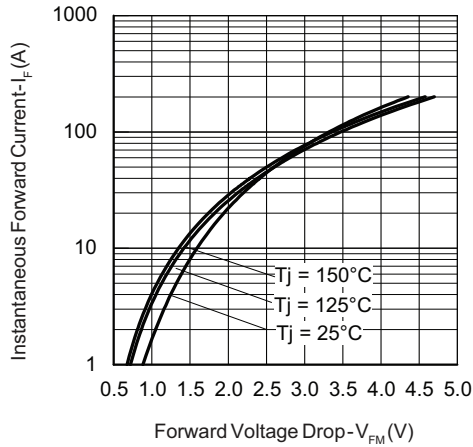


Fig. 1 - Typical Forward Voltage Drop Characteristics

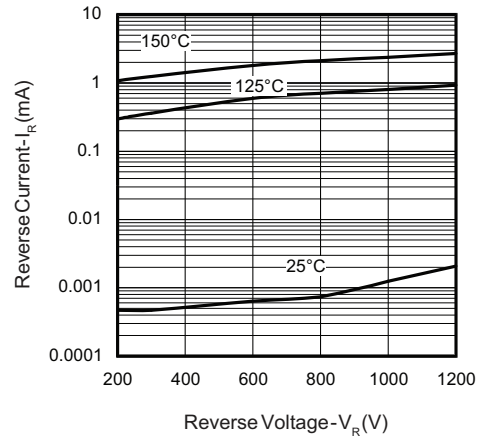


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

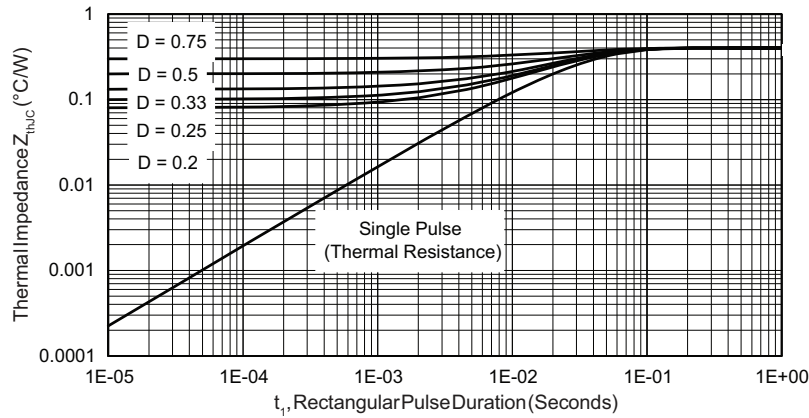
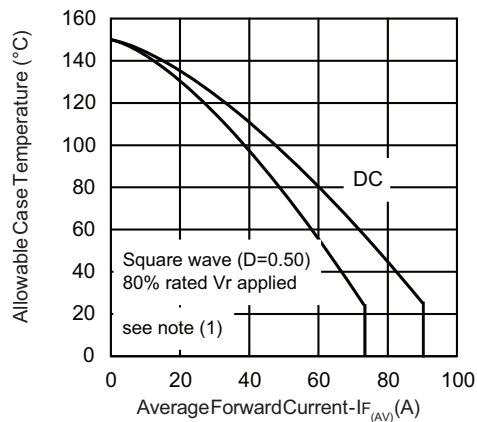

 Fig. 3 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

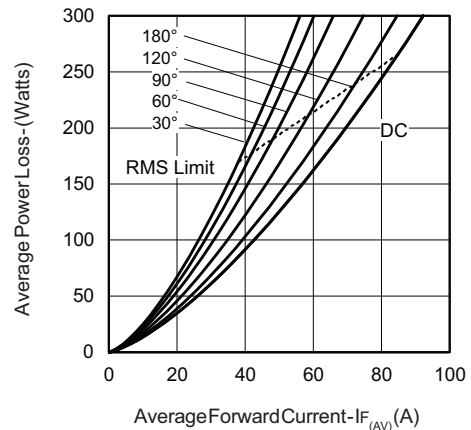


Fig. 5 - Forward Power Loss Characteristics

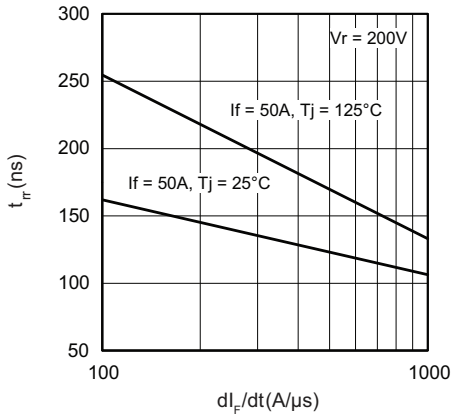


Fig. 6 - Typical Reverse Recovery Time vs.  $dI_F/dt$

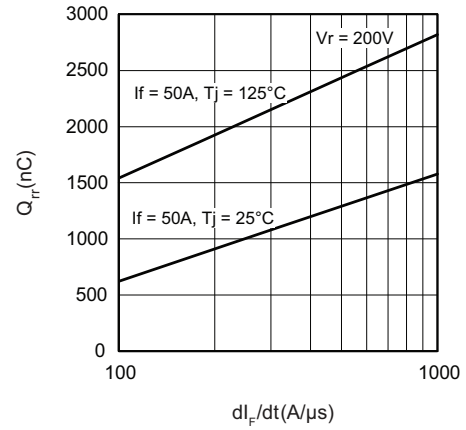


Fig. 7 - Typical Stored Charge vs.  $dI_F/dt$

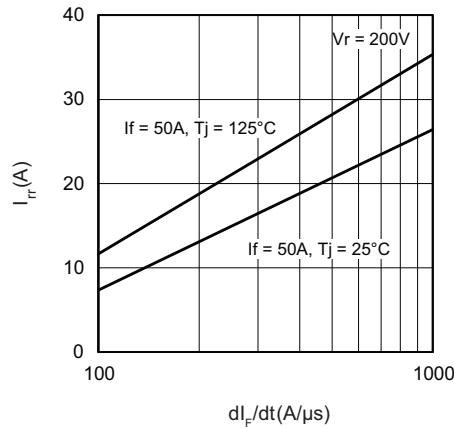


Fig. 8 - Typical Peak Recovery Current vs.  $dI_F/dt$

**Note**

- (1) Formula used:  $T_C = T_J - (P_d + P_{d_{REV}}) \times R_{thJC}$ ;  
 $P_d$  = Forward power loss =  $I_{F(AV)} \times V_{FM}$  at  $(I_{F(AV)}/D)$  (see fig. 5);  
 $P_{d_{REV}}$  = Inverse power loss =  $V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1}$  = Rated  $V_R$

**HEXFRED®**  
 Ultrafast Soft Recovery Diode, 60 A

Vishay Semiconductors

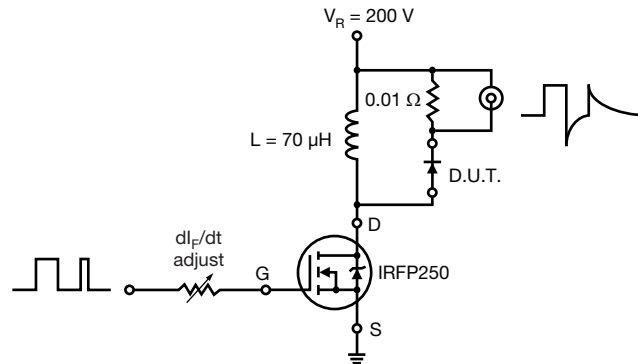
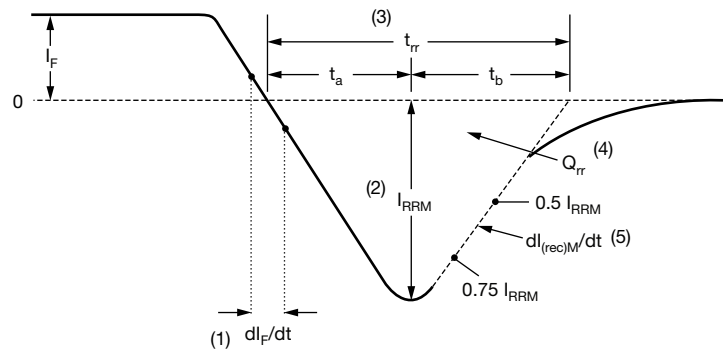


Fig. 9 - Reverse Recovery Parameter Test Circuit


 (1)  $di_F/dt$  - rate of change of current through zero crossing

 (2)  $I_{RRM}$  - peak reverse recovery current

 (3)  $t_{rr}$  - reverse recovery time measured from zero crossing point of negative going  $I_F$  to point where a line passing through  $0.75 I_{RRM}$  and  $0.50 I_{RRM}$  extrapolated to zero current.

 (4)  $Q_{rr}$  - area under curve defined by  $t_{rr}$  and  $I_{RRM}$ 

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

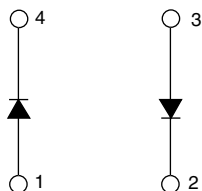
 (5)  $di_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

Fig. 10 - Reverse Recovery Waveform and Definitions

## ORDERING INFORMATION TABLE

|             |           |          |                               |           |            |   |
|-------------|-----------|----------|-------------------------------|-----------|------------|---|
| Device code | <b>HF</b> | <b>A</b> | <b>60</b>                     | <b>EA</b> | <b>120</b> | <b>P</b>  |
|             | ①         | ②        | ③                             | ④         | ⑤          | ⑥   |
|             | <b>1</b>  | -        | HEXFRED® family               | <b>2</b>  | -          | Process designator (A = Electron irradiated)          |
|             | <b>3</b>  | -        | Average current (60 = 60 A)   | <b>4</b>  | -          | Package outline (EA = SOT-227, 2 diodes antiparallel) |
|             | <b>5</b>  | -        | Voltage rating (120 = 1200 V) | <b>6</b>  | -          | P = Lead (Pb)-free                                    |

## CIRCUIT CONFIGURATION

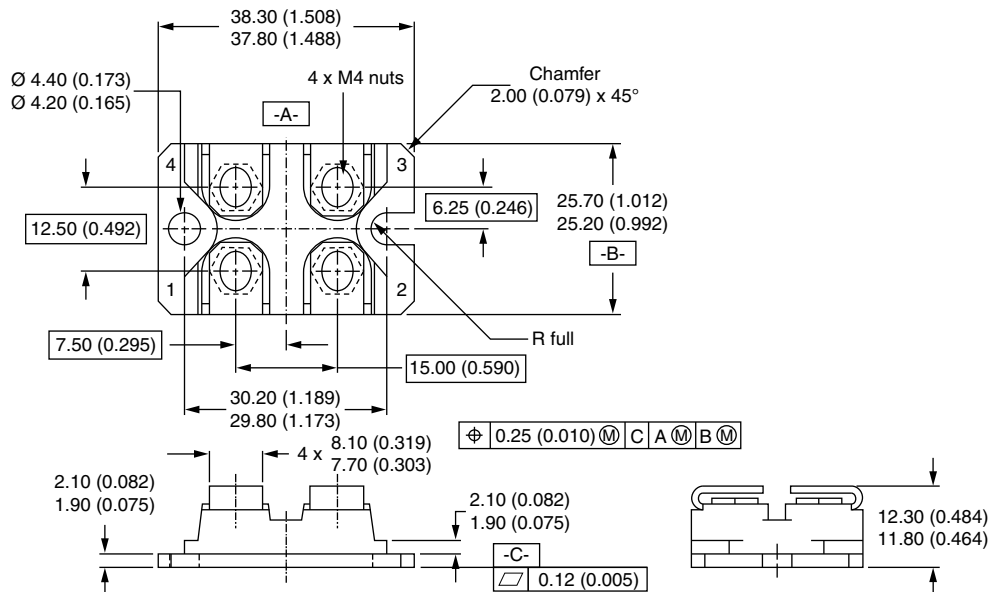


### LINKS TO RELATED DOCUMENTS

|                       |  |
|-----------------------|--|
| Dimensions            | <a href="http://www.vishay.com/doc?95036">www.vishay.com/doc?95036</a> |
| Packaging information | <a href="http://www.vishay.com/doc?95037">www.vishay.com/doc?95037</a> |

## SOT-227

**DIMENSIONS** in millimeters (inches)



**Notes**

- Dimensioning and tolerancing per ANSI Y14.5M-1982
- Controlling dimension: millimeter



## Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk and agree to fully indemnify and hold Vishay and its distributors harmless from and against any and all claims, liabilities, expenses and damages arising or resulting in connection with such use or sale, including attorneys fees, even if such claim alleges that Vishay or its distributor was negligent regarding the design or manufacture of the part. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.